BAS70LT1G, NSVBAS70LT1G

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS ($T_J = 150^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit	
Forward Current	١ _F	70	mA	
Non–Repetitive Peak Forward Surge Current (t \leq 1.0 s)	I _{FSM}	100	mA	
Reverse Voltage	V _R	70	V	
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	225 1.8	mW mW/°C	
Operating Junction and Storage Temperature Range	T _{J,} T _{stg}	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

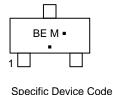
www.onsemi.com

70 VOLTS SCHOTTKY BARRIER DIODES





MARKING DIAGRAM



BE Specific Device Co M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

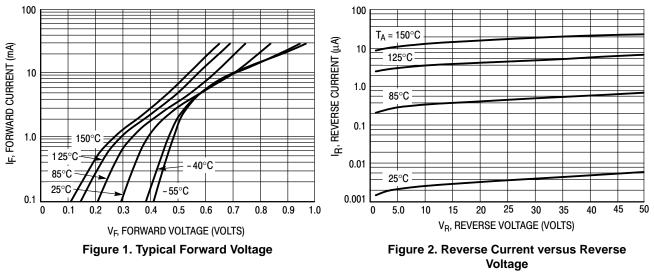
Device	Package	Shipping [†]
BAS70LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVBAS70LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BAS70LT1G, NSVBAS70LT1G

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage $(I_R = 10 \ \mu A)$	V _{(BR)R}	70	_	V
Total Capacitance ($V_R = 0 V, f = 1.0 MHz$)	C _T	_	2.0	pF
Reverse Leakage $(V_R = 50 V)$ $(V_R = 70 V)$	۱ _R		0.1 10	μΑ
Forward Voltage (I _F = 1.0 mA)	V _F	_	410	mV
Forward Voltage (I _F = 10 mA)	V _F	-	750	mV
Forward Voltage (I _F = 15 mA)	V _F	_	1.0	V



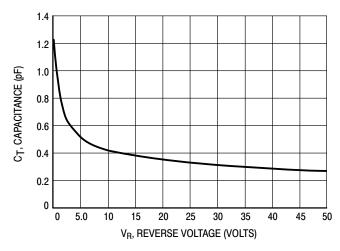
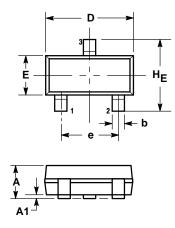


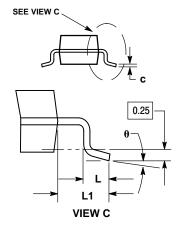
Figure 3. Typical Capacitance

BAS70LT1G, NSVBAS70LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AP





NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
- THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	٥°		10°	Ô٥		10°

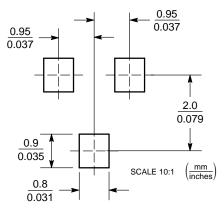
STYLE 8:

PIN 1. ANODE 2. NO CONN

NO CONNECTION
CATHODE

. CATHODE

SOLDERING FOOTPRINT



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